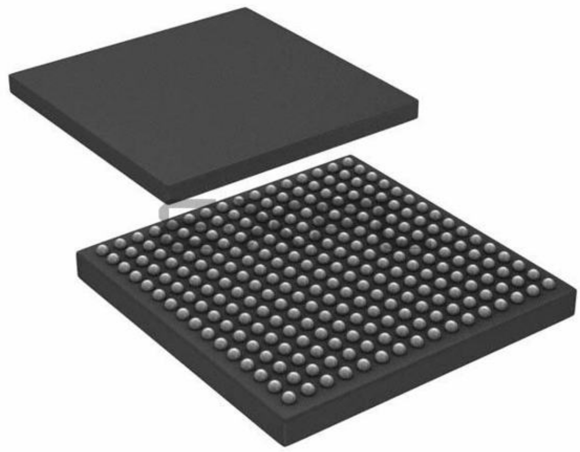


Welcome to E-XFL.COM

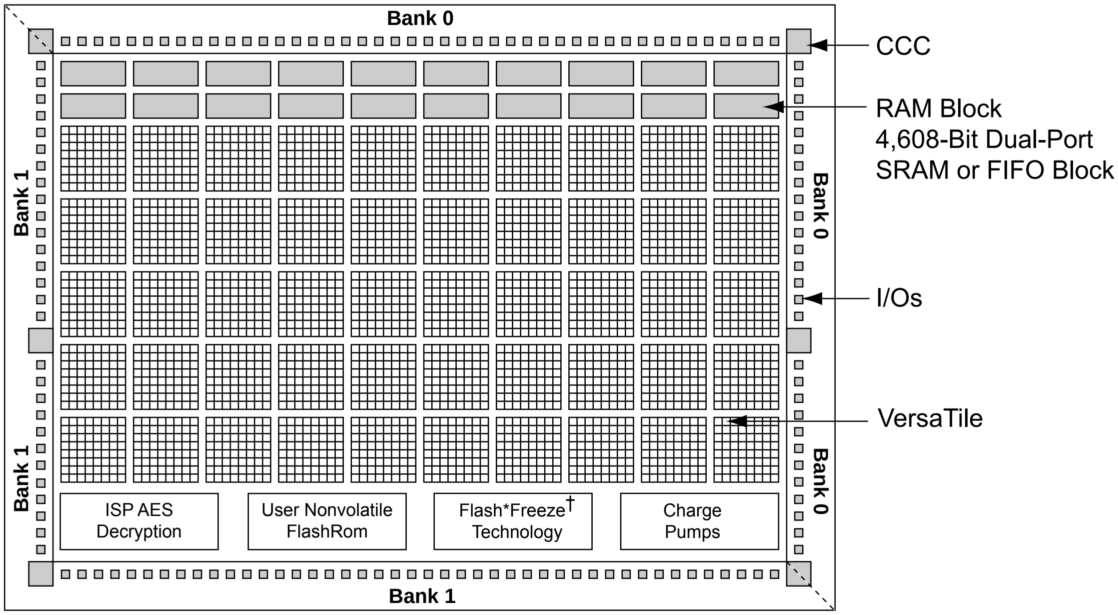
Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

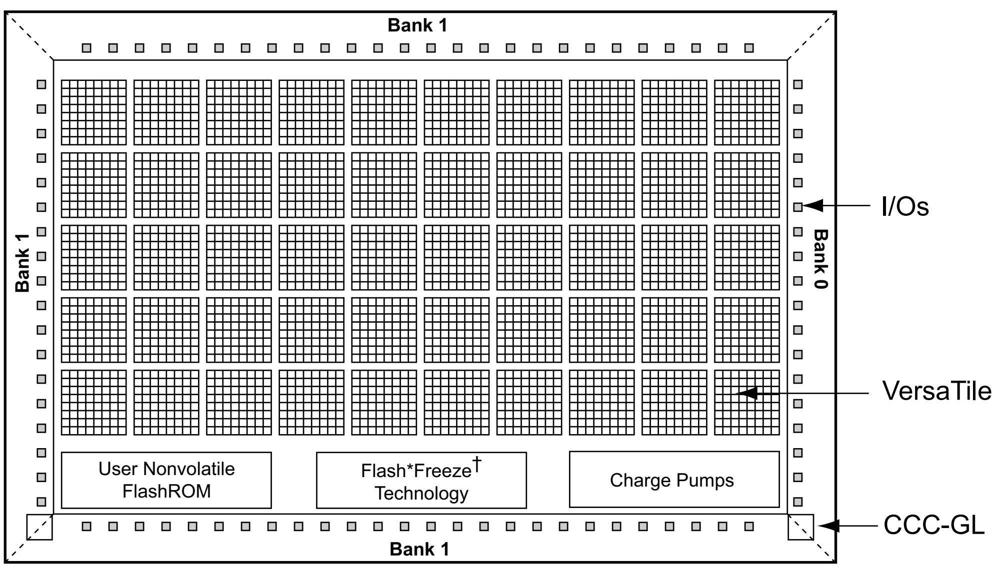
The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	110592
Number of I/O	177
Number of Gates	600000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/a3p600l-1fg256i



Note: † *Flash*Freeze mode is supported on IGLOO devices.*

***Figure 1-3* • IGLOO Device Architecture Overview with Two I/O Banks with RAM and PLL (60 k and 125 k gate densities)**

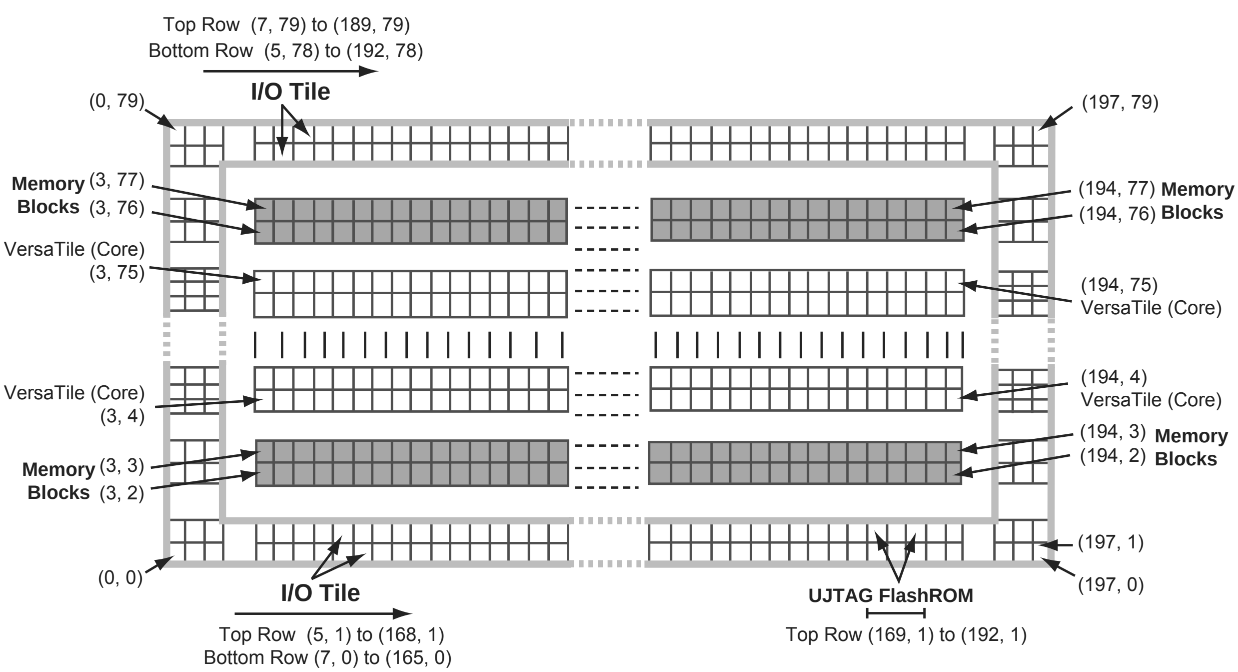


Note: † *Flash*Freeze mode is supported on IGLOO devices.*

***Figure 1-4* • IGLOO Device Architecture Overview with Three I/O Banks (AGLN015, AGLN020, A3PN015, and A3PN020)**

Table 1-4 **• IGLOO nano and ProASIC3 nano Array Coordinates**

Device		VersaTiles		Memory Rows		Entire Die	
		Min.	**Max.**	**Bottom**	**Top**	**Min.**	**Max.**
IGLOO nano	**ProASIC3 nano**	**(x, y)**	**(x, y)**	**(x, y)**	**(x, y)**	**(x, y)**	**(x, y)**
AGLN010	A3P010	(0, 2)	(32, 5)	None	None	(0, 0)	(34, 5)
AGLN015	A3PN015	(0, 2)	(32, 9)	None	None	(0, 0)	(34, 9)
AGLN020	A3PN020	(0, 2)	32, 13)	None	None	(0, 0)	(34, 13)
AGLN060	A3PN060	(3, 2)	(66, 25)	None	(3, 26)	(0, 0)	(69, 29)
AGLN125	A3PN125	(3, 2)	(130, 25)	None	(3, 26)	(0, 0)	(133, 29)
AGLN250	A3PN250	(3, 2)	(130, 49)	None	(3, 50)	(0, 0)	(133, 49)



Note: *The vertical I/O tile coordinates are not shown. West-side coordinates are {(0, 2) to (2, 2)} to {(0, 77) to (2, 77)}; east-side coordinates are {(195, 2) to (197, 2)} to {(195, 77) to (197, 77)}.*

Figure 1-9 **• Array Coordinates for AGL600, AGLE600, A3P600, and A3PE600**

2 – Flash*Freeze Technology and Low Power Modes

Flash*Freeze Technology and Low Power Modes

Microsemi IGLOO,® IGLOO nano, IGLOO PLUS, ProASIC®3L, and Radiation-Tolerant (RT) ProASIC3 FPGAs with Flash*Freeze technology are designed to meet the most demanding power and area challenges of today's portable electronics products with a reprogrammable, small-footprint, full-featured flash FPGA. These devices offer lower power consumption in static and dynamic modes, utilizing the unique Flash*Freeze technology, than any other FPGA or CPLD.

IGLOO, IGLOO nano, IGLOO PLUS, ProASIC3L, and RT ProASIC3 devices offer various power-saving modes that enable every system to utilize modes that achieve the lowest total system power. Low Power Active capability (static idle) allows for ultra-low power consumption while the device is operational in the system by maintaining SRAM, registers, I/Os, and logic functions.

Flash*Freeze technology provides an ultra-low power static mode (Flash*Freeze mode) that retains all SRAM and register information with rapid recovery to Active (operating) mode. IGLOO nano and IGLOO PLUS devices have an additional feature when operating in Flash*Freeze mode, allowing them to retain I/O states as well as SRAM and register states. This mechanism enables the user to quickly (within 1 µs) enter and exit Flash*Freeze mode by activating the Flash*Freeze (FF) pin while all power supplies are kept in their original states. In addition, I/Os and clocks connected to the FPGA can still be toggled without impact on device power consumption. While in Flash*Freeze mode, the device retains all core register states and SRAM information. This mode can be configured so that no power is consumed by the I/O banks, clocks, JTAG pins, or PLLs; and the IGLOO and IGLOO PLUS devices consume as little as 5 µW, while IGLOO nano devices consume as little as 2 µW. Microsemi offers a state management IP core to aid users in gating clocks and managing data before entering Flash*Freeze mode.

This document will guide users in selecting the best low power mode for their applications, and introduces Microsemi's Flash*Freeze management IP core.

Table 2-4 summarizes the Flash*Freeze mode implementations.

Table 2-4 • **Flash*Freeze Mode Usage**

Flash*Freeze Mode Type	Description	Flash*Freeze Pin State	Instantiate ULSICC Macro	LSICC Signal	Operating Mode
1	Flash*Freeze mode is controlled only by the FF pin.	Deasserted	No	N/A	Normal operation
		Asserted	No	N/A	Flash*Freeze mode
2	Flash*Freeze mode is controlled by the FF pin and LSICC signal.	"Don't care"	Yes	Deasserted	Normal operation
		Deasserted	Yes	"Don't care"	Normal operation
		Asserted	Yes	Asserted	Flash*Freeze mode

*Note: Refer to Table 2-3 on page 26 for Flash*Freeze pin and LSICC signal assertion and deassertion values.*

IGLOO, ProASIC3L, and RT ProASIC3 I/O State in Flash*Freeze Mode

In IGLOO and ProASIC3L devices, when the device enters Flash*Freeze mode, I/Os become tristated. If the weak pull-up or pull-down feature is used, the I/Os will maintain the configured weak pull-up or pull-down status. This feature enables the design to set the I/O state to a certain level that is determined by the pull-up/-down configuration.

Table 2-5 shows the I/O pad state based on the configuration and buffer type.

Note that configuring weak pull-up or pull-down for the FF pin is not allowed. The FF pin can be configured as a Schmitt trigger input in IGLOOe, IGLOO nano, IGLOO PLUS, and ProASIC3EL devices.

Table 2-5 • **IGLOO, ProASIC3L, and RT ProASIC3 Flash*Freeze Mode (type 1 and type 2)—I/O Pad State**

Buffer Type		I/O Pad Weak Pull-Up/-Down	I/O Pad State in Flash*Freeze Mode
Input/Global		Enabled	Weak pull-up/pull-down*
		Disabled	Tristate*
Output		Enabled	Weak pull-up/pull-down
		Disabled	Tristate
Bidirectional / Tristate Buffer	E = 0 (input/tristate)	Enabled	Weak pull-up/pull-down*
		Disabled	Tristate*
	E = 1 (output)	Enabled	Weak pull-up/pull-down
		Disabled	Tristate

* *Internal core logic driven by this input/global buffer will be tied High as long as the device is in Flash*Freeze mode.*

Sleep and Shutdown Modes

Sleep Mode

IGLOO, IGLOO nano, IGLOO PLUS, ProASIC3L, and RT ProASIC3 FPGAs support Sleep mode when device functionality is not required. In Sleep mode, V_{CC} (core voltage), V_{JTAG} (JTAG DC voltage), and VPUMP (programming voltage) are grounded, resulting in the FPGA core being turned off to reduce power consumption. While the device is in Sleep mode, the rest of the system can still be operating and driving the input buffers of the device. The driven inputs do not pull up the internal power planes, and the current draw is limited to minimal leakage current.

Table 2-7 shows the power supply status in Sleep mode.

Table 2-7 • **Sleep Mode—Power Supply Requirement for IGLOO, IGLOO nano, IGLOO PLUS, ProASIC3L, and RT ProASIC3 Devices**

Power Supplies	Power Supply State
VCC	Powered off
VCCI = VMV	Powered on
VJTAG	Powered off
VPUMP	Powered off

Refer to the "Power-Up/-Down Behavior" section on page 33 for more information about I/O states during Sleep mode and the timing diagram for entering and exiting Sleep mode.

Shutdown Mode

Shutdown mode is supported for all IGLOO nano and IGLOO PLUS devices as well the following IGLOO/e devices: AGL015, AGL030, AGLE600, AGLE3000, and A3PE3000L. Shutdown mode can be used by turning off all power supplies when the device function is not needed. Cold-sparing and hot-insertion features enable these devices to be powered down without turning off the entire system. When power returns, the live-at-power-up feature enables operation of the device after reaching the voltage activation point.

3 – Global Resources in Low Power Flash Devices

Introduction

IGLOO, Fusion, and ProASIC3 FPGA devices offer a powerful, low-delay VersaNet global network scheme and have extensive support for multiple clock domains. In addition to the Clock Conditioning Circuits (CCCs) and phase-locked loops (PLLs), there is a comprehensive global clock distribution network called a VersaNet global network. Each logical element (VersaTile) input and output port has access to these global networks. The VersaNet global networks can be used to distribute low-skew clock signals or high-fanout nets. In addition, these highly segmented VersaNet global networks contain spines (the vertical branches of the global network tree) and ribs that can reach all the VersaTiles inside their region. This allows users the flexibility to create low-skew local clock networks using spines. This document describes VersaNet global networks and discusses how to assign signals to these global networks and spines in a design flow. Details concerning low power flash device PLLs are described in the "Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" section on page 77. This chapter describes the low power flash devices' global architecture and uses of these global networks in designs.

Global Architecture

Low power flash devices offer powerful and flexible control of circuit timing through the use of global circuitry. Each chip has up to six CCCs, some with PLLs.

- In IGLOOe, ProASIC3EL, and ProASIC3E devices, all CCCs have PLLs—hence, 6 PLLs per device (except the PQ208 package, which has only 2 PLLs).
- In IGLOO, IGLOO nano, IGLOO PLUS, ProASIC3, and ProASIC3L devices, the west CCC contains a PLL core (except in 10 k through 30 k devices).
- In Fusion devices, the west CCC also contains a PLL core. In the two larger devices (AFS600 and AFS1500), the west and east CCCs each contain a PLL.

Refer to Table 4-6 on page 100 for details. Each PLL includes delay lines, a phase shifter (0°, 90°, 180°, 270°), and clock multipliers/dividers. Each CCC has all the circuitry needed for the selection and interconnection of inputs to the VersaNet global network. The east and west CCCs each have access to three chip global lines on each side of the chip (six chip global lines total). The CCCs at the four corners each have access to three quadrant global lines in each quadrant of the chip (except in 10 k through 30 k gate devices).

The nano 10 k, 15 k, and 20 k devices support four VersaNet global resources, and 30 k devices support six global resources. The 10 k through 30 k devices have simplified CCCs called CCC-GLs.

The flexible use of the VersaNet global network allows the designer to address several design requirements. User applications that are clock-resource-intensive can easily route external or gated internal clocks using VersaNet global routing networks. Designers can also drastically reduce delay penalties and minimize resource usage by mapping critical, high-fanout nets to the VersaNet global network.

Note: Microsemi recommends that you choose the appropriate global pin and use the appropriate global resource so you can realize these benefits.

The following sections give an overview of the VersaNet global network, the structure of the global network, access point for the global networks, and the clock aggregation feature that enables a design to have very low clock skew using spines.

Global Resource Support in Flash-Based Devices

The flash FPGAs listed in Table 3-1 support the global resources and the functions described in this document.

***Table 3-1* • Flash-Based FPGAs**

Series	Family*	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
	IGLOO nano	The industry's lowest-power, smallest-size solution
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM® Cortex™-M1 soft processors, and flash memory into a monolithic device

Note: **The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.*

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO products as listed in Table 3-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 3-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

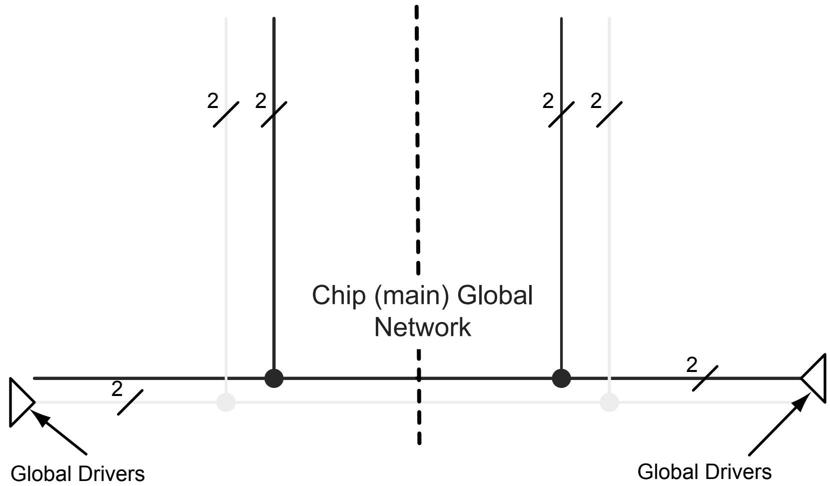


Figure 3-2 **• Simplified VersaNet Global Network (30 k gates and below)**

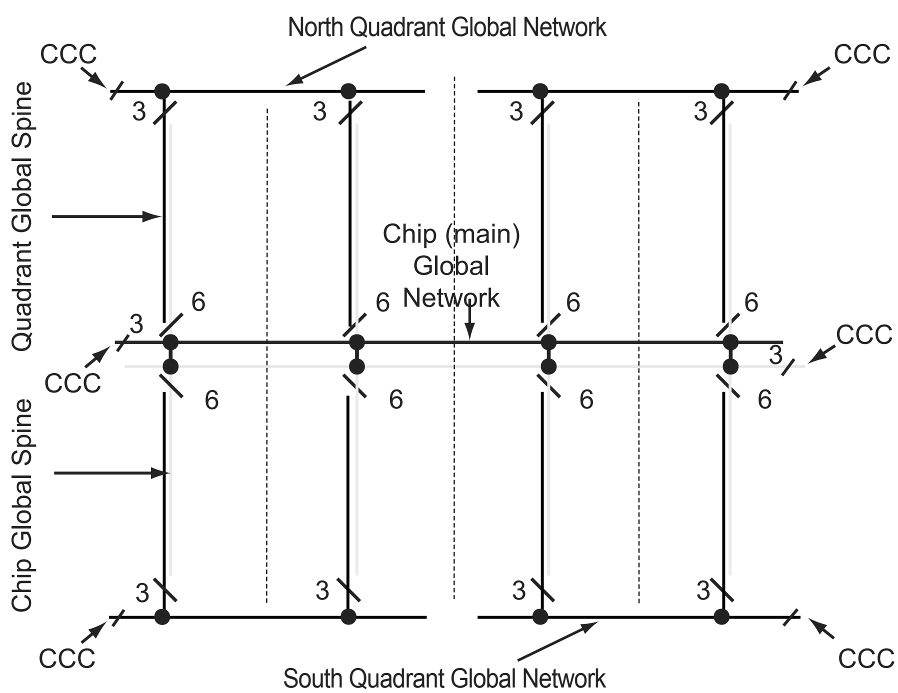


Figure 3-3 **• Simplified VersaNet Global Network (60 k gates and above)**

Spine Access

The physical location of each spine is identified by the letter T (top) or B (bottom) and an accompanying number (T*n* or B*n*). The number *n* indicates the horizontal location of the spine; 1 refers to the first spine on the left side of the die. Since there are six chip spines in each spine tree, there are up to six spines available for each combination of T (or B) and *n* (for example, six T1 spines). Similarly, there are three quadrant spines available for each combination of T (or B) and *n* (for example, four T1 spines), as shown in Figure 3-7.

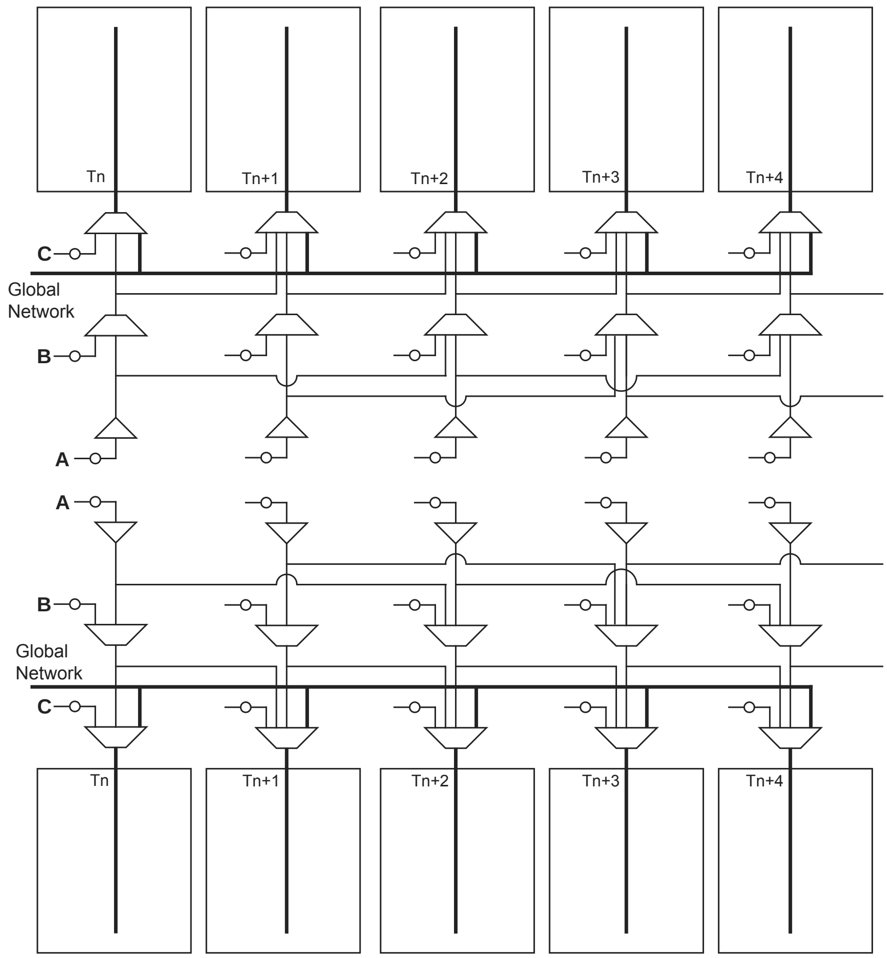


Figure 3-7 **• Chip Global Aggregation**

A spine is also called a local clock network, and is accessed by the dedicated global MUX architecture. These MUXes define how a particular spine is driven. Refer to Figure 3-8 on page 60 for the global MUX architecture. The MUXes for each chip global spine are located in the middle of the die. Access to the top and bottom chip global spine is available from the middle of the die. There is no control dependency between the top and bottom spines. If a top spine, T1, of a chip global network is assigned to a net, B1 is not wasted and can be used by the global clock network. The signal assigned only to the top or bottom spine cannot access the middle two rows of the architecture. However, if a spine is using the top and bottom at the same time (T1 and B1, for instance), the previous restriction is lifted.

The MUXes for each quadrant global spine are located in the north and south sides of the die. Access to the top and bottom quadrant global spines is available from the north and south sides of the die. Since the MUXes for quadrant spines are located in the north and south sides of the die, you should not try to drive T1 and B1 quadrant spines from the same signal.

Implementing EXTFB in ProASIC3/E Devices

When the external feedback (EXTFB) signal of the PLL in the ProASIC3/E devices is implemented, the phase detector of the PLL core receives the reference clock (CLKA) and EXTFB as inputs. EXTFB must be sourced as an INBUF macro and located at the global/chip clock location associated with the target PLL by Designer software. EXTFB cannot be sourced from the FPGA fabric.

The following example shows CLKA and EXTFB signals assigned to two global I/Os in the same global area of ProASIC3E device.

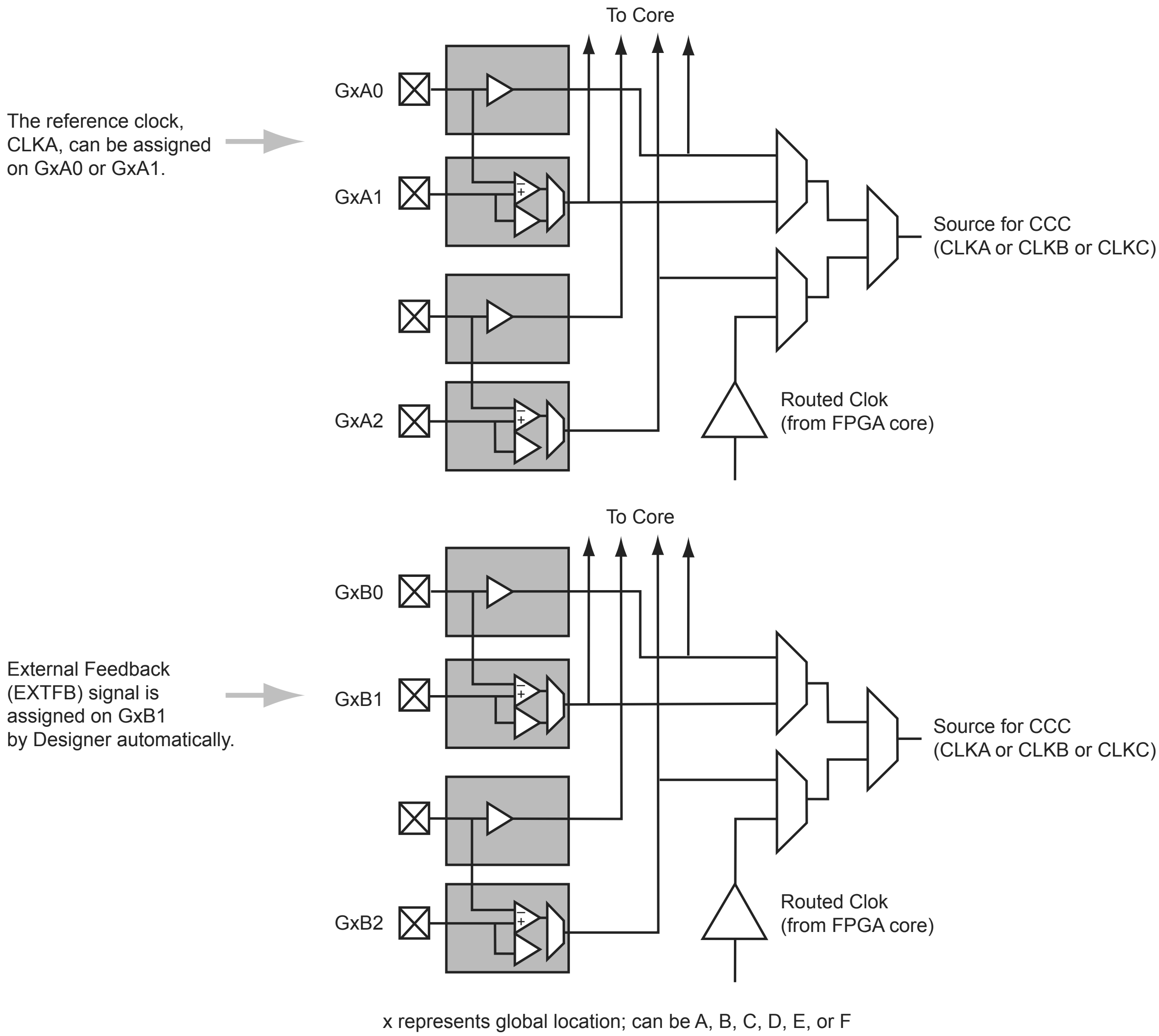


Figure 4-5 • **CLKA and EXTFB Assigned to Global I/Os**

Loading the Configuration Register

The most important part of CCC dynamic configuration is to load the shift register properly with the configuration bits. There are different ways to access and load the configuration shift register:

- JTAG interface
- Logic core
- Specific I/O tiles

JTAG Interface

The JTAG interface requires no additional I/O pins. The JTAG TAP controller is used to control the loading of the CCC configuration shift register.

Low power flash devices provide a user interface macro between the JTAG pins and the device core logic. This macro is called UJTAG. A user should instantiate the UJTAG macro in his design to access the configuration register ports via the JTAG pins.

For more information on CCC dynamic reconfiguration using UJTAG, refer to the "UJTAG Applications in Microsemi's Low Power Flash Devices" section on page 363.

Logic Core

If the logic core is employed, the user must design a module to provide the configuration data and control the shifting and updating of the CCC configuration shift register. In effect, this is a user-designed TAP controller, which requires additional chip resources.

Specific I/O Tiles

If specific I/O tiles are used for configuration, the user must provide the external equivalent of a TAP controller. This does not require additional core resources but does use pins.

Shifting the Configuration Data

To enter a new configuration, all 81 bits must shift in via SDIN. After all bits are shifted, SSHIFT must go LOW and SUPDATE HIGH to enable the new configuration. For simulation purposes, bits <71:73> and <77:80> are "don't care."

The SUPDATE signal must be LOW during any clock cycle where SSHIFT is active. After SUPDATE is asserted, it must go back to the LOW state until a new update is required.

PLL Configuration Bits Description

Table 4-8 **• Configuration Bit Descriptions for the CCC Blocks**

Config. Bits	Signal	Name	Description
<88:87>	GLMUXCFG [1:0][1]	NGMUX configuration	The configuration bits specify the input clocks to the NGMUX (refer to Table 4-17 on page 110).[2]
86	OCDIVHALF[1]	Division by half	When the PLL is bypassed, the 100 MHz RC oscillator can be divided by the divider factor in Table 4-18 on page 111.
85	OBDIVHALF[1]	Division by half	When the PLL is bypassed, the 100 MHz RC oscillator can be divided by a 0.5 factor (refer to Table 4-18 on page 111).
84	OADIVHALF[1]	Division by half	When the PLL is bypassed, the 100 MHz RC oscillator can be divided by certain 0.5 factor (refer to Table 4-16 on page 110).

Notes:

1. *The <88:81> configuration bits are only for the Fusion dynamic CCC.*
2. *This value depends on the input clock source, so Layout must complete before these bits can be set. After completing Layout in Designer, generate the "CCC_Configuration" report by choosing **Tools** > **Report** > **CCC_Configuration**. The report contains the appropriate settings for these bits.*

global assignments are not allocated properly. See the "Physical Constraints for Quadrant Clocks" section for information on assigning global signals to the quadrant clock networks.

Promoted global signals will be instantiated with CLKINT macros to drive these signals onto the global network. This is automatically done by Designer when the Auto-Promotion option is selected. If the user wishes to assign the signals to the quadrant globals instead of the default chip globals, this can done by using ChipPlanner, by declaring a physical design constraint (PDC), or by importing a PDC file.

Physical Constraints for Quadrant Clocks

If it is necessary to promote global clocks (CLKBUF, CLKINT, PLL, CLKDLY) to quadrant clocks, the user can define PDCs to execute the promotion. PDCs can be created using PDC commands (pre-compile) or the MultiView Navigator (MVN) interface (post-compile). The advantage of using the PDC flow over the MVN flow is that the Compile stage is able to automatically promote any regular net to a global net before assigning it to a quadrant. There are three options to place a quadrant clock using PDC commands:

- Place a clock core (not hardwired to an I/O) into a quadrant clock location.
- Place a clock core (hardwired to an I/O) into an I/O location (set_io) or an I/O module location (set_location) that drives a quadrant clock location.
- Assign a net driven by a regular net or a clock net to a quadrant clock using the following command:

  ```
  assign_local_clock -net <net name> -type quadrant <quadrant clock region>
  ```

  where

  `<net name>` is the name of the net assigned to the local user clock region.

  `<quadrant clock region>` defines which quadrant the net should be assigned to. Quadrant clock regions are defined as UL (upper left), UR (upper right), LL (lower left), and LR (lower right).

Note: If the net is a regular net, the software inserts a CLKINT buffer on the net.

For example:

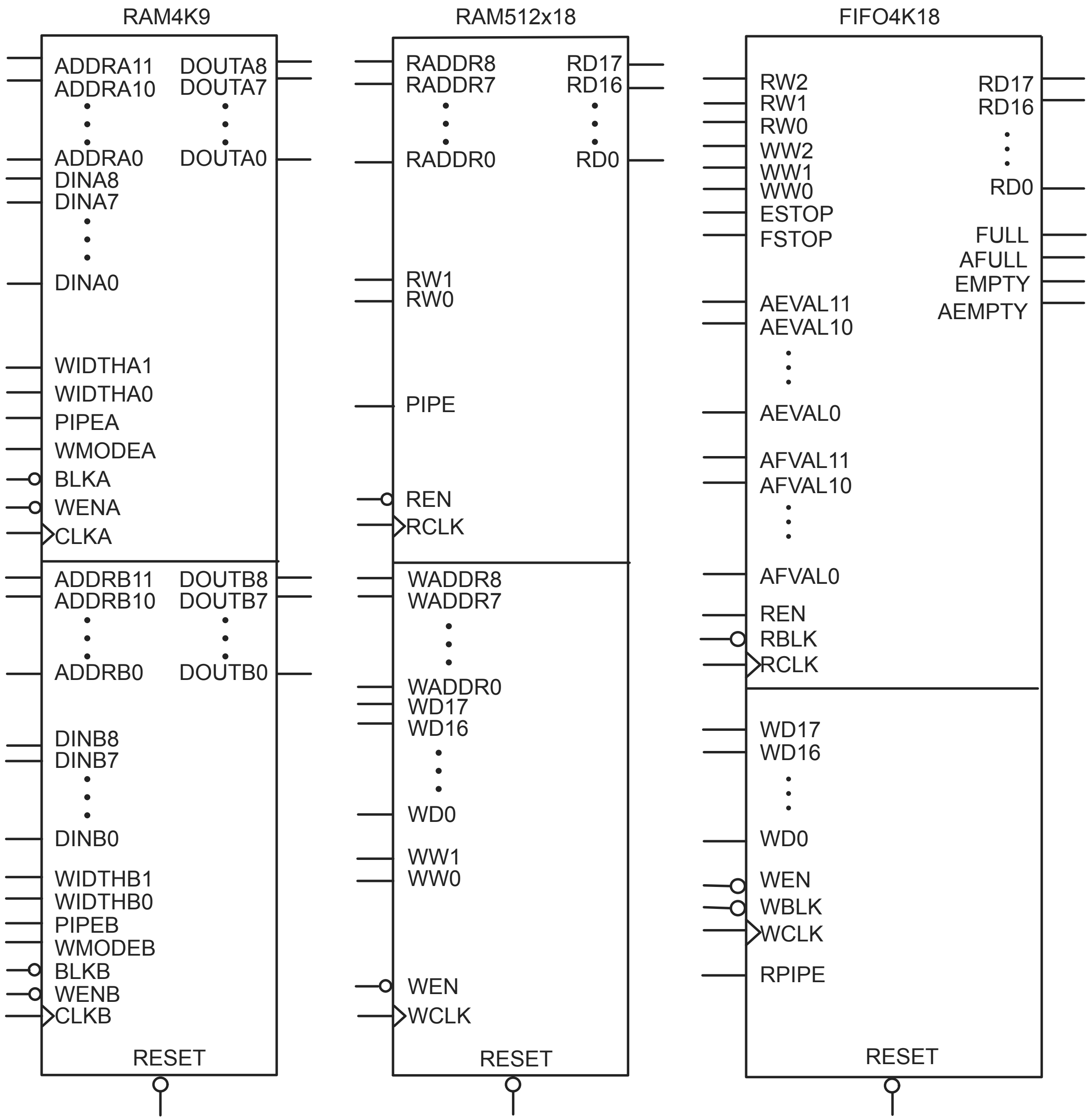
```
assign_local_clock -net localReset -type quadrant UR
```

Keep in mind the following when placing quadrant clocks using MultiView Navigator:

Hardwired I/O–Driven CCCs

- Find the associated clock input port under the Ports tab, and place the input port at one of the Gmn* locations using PinEditor or I/O Attribute Editor, as shown in Figure 4-32.

Figure 4-32 **• Port Assignment for a CCC with Hardwired I/O Clock Input**



Notes:

1. *Automotive ProASIC3 devices restrict RAM4K9 to a single port or to dual ports with the same clock 180° out of phase (inverted) between clock pins. In single-port mode, inputs to port B should be tied to ground to prevent errors during compile. This warning applies only to automotive ProASIC3 parts of certain revisions and earlier. Contact Technical Support at soc_tech@microsemi.com for information on the revision number for a particular lot and date code.*
2. *For FIFO4K18, the same clock 180° out of phase (inverted) between clock pins should be used.*

Figure 6-3 **• Supported Basic RAM Macros**

I/O Bank Structure

Low power flash device I/Os are divided into multiple technology banks. The number of banks is device-dependent. The IGLOOe, ProASIC3EL, and ProASIC3E devices have eight banks (two per side); and IGLOO, ProASIC3L, and ProASIC3 devices have two to four banks. Each bank has its own V**CCI** power supply pin. Multiple I/O standards can co-exist within a single I/O bank.

In IGLOOe, ProASIC3EL, and ProASIC3E devices, each I/O bank is subdivided into VREF minibanks. These are used by voltage-referenced I/Os. VREF minibanks contain 8 to 18 I/Os. All I/Os in a given minibank share a common VREF line (only one VREF pin is needed per VREF minibank). Therefore, if an I/O in a VREF minibank is configured as a VREF pin, the remaining I/Os in that minibank will be able to use the voltage assigned to that pin. If the location of the VREF pin is selected manually in the software, the user must satisfy VREF rules (refer to the "I/O Software Control in Low Power Flash Devices" section on page 251). If the user does not pick the VRE_F pin manually, the software automatically assigns it.

Figure 7-3 is a snapshot of a section of the I/O ring, showing the basic elements of an I/O tile, as viewed from the Designer place-and-route tool's MultiView Navigator (MVN).

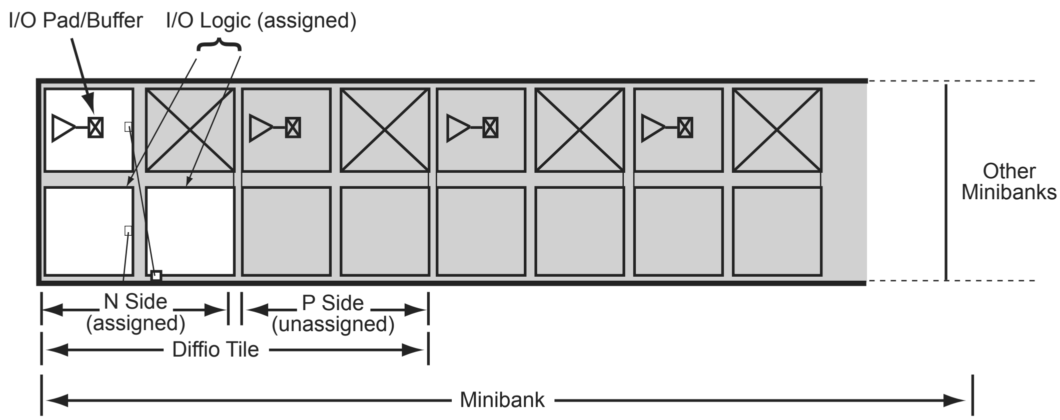


Figure 7-3 **• Snapshot of an I/O Tile**

Low power flash device I/Os are implemented using two tile types: I/O and differential I/O (diffio).

The diffio tile is built up using two I/O tiles, which form an I/O pair (P side and N side). These I/O pairs are used according to differential I/O standards. Both the P and N sides of the diffio tile include an I/O buffer and two I/O logic blocks (auxiliary and main logic).

Every minibank (E devices only) is built up from multiple diffio tiles. The number of the minibank depends on the different-size dies. Refer to the "I/O Architecture" section on page 181 for an illustration of the minibank structure.

Figure 7-4 on page 183 shows a simplified diagram of the I/O buffer circuitry. The Output Enable signal (OE) enables the output buffer to pass the signal from the core logic to the pin. The output buffer contains ESD protection circuitry, an n-channel transistor that shunts all ESD surges (up to the limit of the device ESD specification) to GND. This transistor also serves as an output pull-down resistor.

Each output buffer also contains programmable slew rate, drive strength, programmable power-up state (pull-up/-down resistor), hot-swap, 5 V tolerance, and clamp diode control circuitry. Multiple flash switches (not shown in Figure 7-4 on page 183) are programmed by user selections in the software to activate different I/O features.

IGLOO and ProASIC3

For boards and cards with three levels of staging, card power supplies must have time to reach their final values before the I/Os are connected. Pay attention to the sizing of power supply decoupling capacitors on the card to ensure that the power supplies are not overloaded with capacitance.

Cards with three levels of staging should have the following sequence:

- Grounds
- Powers
- I/Os and other pins

For Level 3 and Level 4 compliance with the 30K gate device, cards with two levels of staging should have the following sequence:

- Grounds
- Powers, I/Os, and other pins

Cold-Sparing Support

Cold-sparing refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

The resistor value is calculated based on the decoupling capacitance on a given power supply. The RC constant should be greater than 3 µs.

To remove resistor current during operation, it is suggested that the resistor be disconnected (e.g., with an NMOS switch) from the power supply after the supply has reached its final value. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 373 for details on cold-sparing.

Cold-sparing means that a subsystem with no power applied (usually a circuit board) is electrically connected to the system that is in operation. This means that all input buffers of the subsystem must present very high input impedance with no power applied so as not to disturb the operating portion of the system.

The 30 k gate devices fully support cold-sparing, since the I/O clamp diode is always off (see Table 7-12 on page 193). If the 30 k gate device is used in applications requiring cold-sparing, a discharge path from the power supply to ground should be provided. This can be done with a discharge resistor or a switched resistor. This is necessary because the 30K gate devices do not have built-in I/O clamp diodes.

For other IGLOO and ProASIC3 devices, since the I/O clamp diode is always active, cold-sparing can be accomplished either by employing a bus switch to isolate the device I/Os from the rest of the system or by driving each I/O pin to 0 V. If the resistor is chosen, the resistor value must be calculated based on decoupling capacitance on a given power supply on the board (this decoupling capacitance is in parallel with the resistor). The RC time constant should ensure full discharge of supplies before cold-sparing functionality is required. The resistor is necessary to ensure that the power pins are discharged to ground every time there is an interruption of power to the device.

IGLOOe and ProASIC3E devices support cold-sparing for all I/O configurations. Standards, such as PCI, that require I/O clamp diodes can also achieve cold-sparing compliance, since clamp diodes get disconnected internally when the supplies are at 0 V.

When targeting low power applications, I/O cold-sparing may add additional current if a pin is configured with either a pull-up or pull-down resistor and driven in the opposite direction. A small static current is induced on each I/O pin when the pin is driven to a voltage opposite to the weak pull resistor. The current is equal to the voltage drop across the input pin divided by the pull resistor. Refer to the "Detailed I/O DC Characteristics" section of the appropriate family datasheet for the specific pull resistor value for the corresponding I/O standard.

For example, assuming an LVTTL 3.3 V input pin is configured with a weak pull-up resistor, a current will flow through the pull-up resistor if the input pin is driven LOW. For LVTTL 3.3 V, the pull-up resistor is ~45 kΩ, and the resulting current is equal to 3.3 V / 45 kΩ = 73 µA for the I/O pin. This is true also when a weak pull-down is chosen and the input pin is driven HIGH. This current can be avoided by driving the input LOW when a weak pull-down resistor is used and driving it HIGH when a weak pull-up resistor is used.

This current draw can occur in the following cases:

***Table 8-9* • Hot-Swap Level 1**

Description	Cold-swap
Power Applied to Device	No
Bus State	–
Card Ground Connection	–
Device Circuitry Connected to Bus Pins	–
Example Application	System and card with Microsemi FPGA chip are powered down, and the card is plugged into the system. Then the power supplies are turned on for the system but not for the FPGA on the card.
Compliance of IGLOO and ProASIC3 Devices	30 k gate devices: Compliant Other IGLOO/ProASIC3 devices: Compliant if bus switch used to isolate FPGA I/Os from rest of system IGLOOe/ProASIC3E devices: Compliant I/Os can, but do not have to be set to hot-insertion mode.

***Table 8-10* • Hot-Swap Level 2**

Description	Hot-swap while reset
Power Applied to Device	Yes
Bus State	Held in reset state
Card Ground Connection	Reset must be maintained for 1 ms before, during, and after insertion/removal.
Device Circuitry Connected to Bus Pins	–
Example Application	In the PCI hot-plug specification, reset control circuitry isolates the card busses until the card supplies are at their nominal operating levels and stable.
Compliance of IGLOO and ProASIC3 Devices	30 k gate devices, all IGLOOe/ProASIC3E devices: Compliant I/Os can but do not have to be set to hot-insertion mode. Other IGLOO/ProASIC3 devices: Compliant

Instantiating DDR Registers

Using SmartGen is the simplest way to generate the appropriate RTL files for use in the design. Figure 10-4 shows an example of using SmartGen to generate a DDR SSTL2 Class I input register. SmartGen provides the capability to generate all of the DDR I/O cells as described. The user, through the graphical user interface, can select from among the many supported I/O standards. The output formats supported are Verilog, VHDL, and EDIF.

Figure 10-5 on page 277 through Figure 10-8 on page 280 show the I/O cell configured for DDR using SSTL2 Class I technology. For each I/O standard, the I/O pad is buffered by a special primitive that indicates the I/O standard type.

Figure 10-4 **• Example of Using SmartGen to Generate a DDR SSTL2 Class I Input Register**

errors, but this list is intended to show where problems can occur. FlashPro4/3/3X allows TCK to be lowered from 6 MHz down to 1 MHz to allow you to address some signal integrity problems that may occur with impedance mismatching at higher frequencies. Customers are expected to troubleshoot board-level signal integrity issues by measuring voltages and taking scope plots.

Scan Chain Failure

Normally, the FlashPro4/3/3X Scan Chain command expects to see 0x1 on the TDO pin. If the command reports reading 0x0 or 0x3, it is seeing the TDO pin stuck at 0 or 1. The only time the TDO pin comes out of tristate is when the JTAG TAP state machine is in the Shift-IR or Shift-DR state. If noise or reflections on the TCK or TMS lines have disrupted the correct state transitions, the device's TAP state controller might not be in one of these two states when the programmer tries to read the device. When this happens, the output is floating when it is read and does not match the expected data value. This can also be caused by a broken TDO net. Only a small amount of data is read from the device during the Scan Chain command, so marginal problems may not always show up during this command. Occasionally a faulty programmer can cause intermittent scan chain failures.

Exit 11

This error occurs during the verify stage of programming a device. After programming the design into the device, the device is verified to ensure it is programmed correctly. The verification is done by shifting the programming data into the device. An internal comparison is performed within the device to verify that all switches are programmed correctly. Noise induced by poor signal integrity can disrupt the writes and reads or the verification process and produce a verification error. While technically a verification error, the root cause is often related to signal integrity.

Refer to the *FlashPro User's Guide* for other error messages and solutions. For the most up-to-date known issues and solutions, refer to http://www.microsemi.com/soc/support.

Conclusion

IGLOO, ProASIC3, SmartFusion, and Fusion devices offer a low-cost, single-chip solution that is live at power-up through nonvolatile flash technology. The FlashLock Pass Key and 128-bit AES Key security features enable secure ISP in an untrusted environment. On-chip FlashROM enables a host of new applications, including device serialization, subscription-based applications, and IP addressing. Additionally, as the FlashROM is nonvolatile, all of these services can be provided without battery backup.

Related Documents

User's Guides

FlashPro User's Guide

http://www.microsemi.com/soc/documents/flashpro_ug.pdf

Circuit Verification

The power switching circuit recommended above is implemented on Microsemi's Icicle board (Figure 14-2). On the Icicle board, VJTAGENB is used to control the N-Channel Digital FET; however, this circuit was modified to use TRST instead of VJTAGENB in this application. There are three important aspects of this circuit that were verified:

1. The rise on VCC from 1.2 V to 1.5 V when TRST is HIGH
2. VCC rises to 1.5 V before programming begins.
3. VCC switches from 1.5 V to 1.2 V when TRST is LOW.

Verification Steps

1. The rise on VCC from 1.2 V to 1.5 V when TRST is HIGH.

Figure 14-2 **• Core Voltage on the IGLOO AGL125-QNG132 Device**

In the oscilloscope plots (Figure 14-2), the TRST from FlashPro3 and the VCC core voltage of the IGLOO device are labeled. This plot shows the rise characteristic of the TRST signal from FlashPro3. Once the TRST signal is asserted HIGH, the LTC3025 shown in Figure 14-1 on page 343 senses the increase in voltage and changes the output from 1.2 V to 1.5 V. It takes the circuit approximately 100 μs to respond to TRST and change the voltage to 1.5 V on the VCC core.